SHENZHEN MENGKE ELECTRONICS TECHNOLOGY CO., LTD

TO-252/TO-251 Plastic-Encapsulate schottky barrier diodes

MBR1045CT Dual schottky barrier diodes

R

VR = 45 V

IF(AV) = 10 A

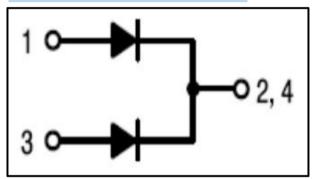
VF ≤ 0.7V

MECHANICALDATA :

- Case: TO-252/251 molded plastic
- Polarity: As marked.
- Mounting Position: Any
- Weight: 0.0655 ounces, 1.859 grams
- Terminals: solder plated,

solderable per MIL-STD-750, Method 2026

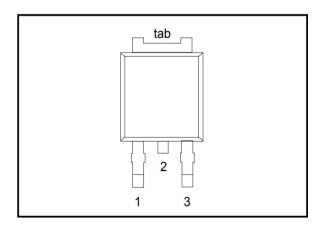
SYMBOL :



FEATURES :

- Plastic package has Underwriters Laboratory
 Flammability Classification 94V-O
 Flame Retardant Epoxy Molding Compound
- Metal silicon junction, majority carrier conduction
- Low power loss, high efficiency
- High current capability
- Guardring for overvlotage protection
- In compliance with EU RoHS 2002/95/EC directives
- For use in low voltage, high frequency inverters
- free wheeling , and polarlity protection applications.

PINNING:				
PIN	DESCRIPTION			
1	anode 1			
2	cathode 1			
3	anode 2			
tab	cathode			





MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load.For capacitive load, derate current by 20%

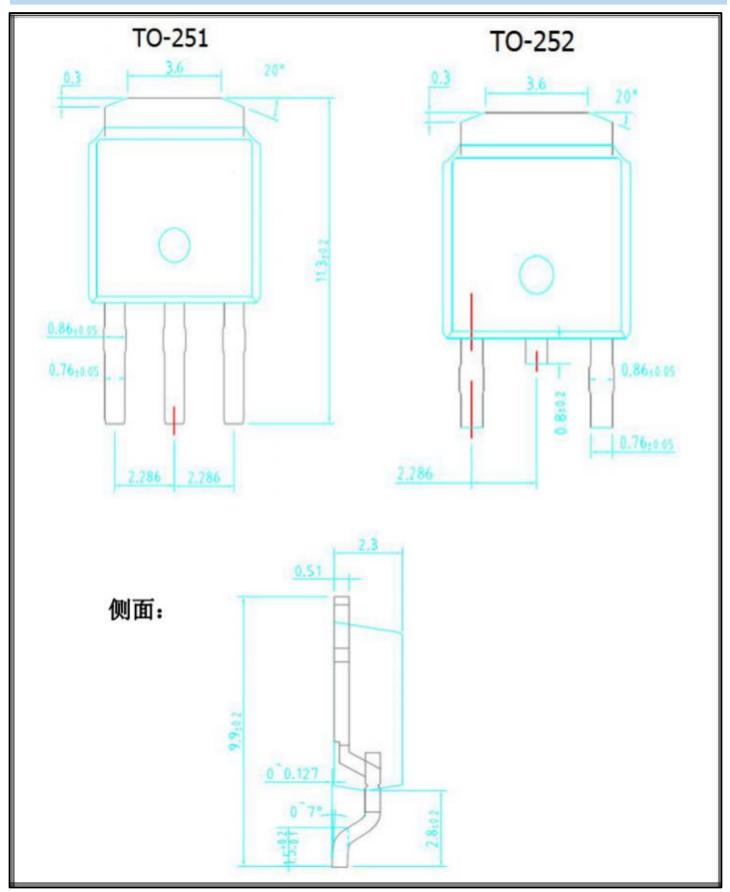
Parameter	Symbol	Test Condition	MIN	TYP	Мах	Unit
Peak Repetitive Reverse Voltage	VRRM				45	V
Maxi mum RMS Voltage	VRMS				31.5	V
Maximum DC Blocking Voltage	VR(DC)				45	V
Average Rectified Forward Current	IF(AV)				10	А
Peak Forward Surge Current:8.3ms single half sine-	IFSM				150	٨
wave superimposed on rated load (JEDEC method)					150	A
Maximum Forward Voltage at 10A,per leg	VF				0.7	V
Maximum DC Reverse Current T=25°C	IR			0.05	0.1	mA
at Rated DC Blocking Voltage T=125 $^\circ\!\!\mathrm{C}$					20	mA
Voltage Rate of Change (Rated VR)	dv/dt				10,000	v/µs
Typical Thermal Resistance	RØJC				2	°C/W
Operating junction temperature	Tj		-65		175	°C
Storage temperature	Tstg		-65		175	°C

Notes :

- 1.Both Bonding and Chip structure are available.
- 2.Pulse Test: Pulse Width = 300 ms, Duty Cycle ≤2.0%
- 3.The heat generated must be less than the thermal conductivity from Junction-to-Ambient: dPD/dTJ < 1/RqJA.



TYPICAL ELEC TRICAL AND THERMAL CHARACTERISTICS





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